

## SOD-323 Plastic-Encapsulate Diode

#### **PRODUCT SUMMARY**

RB551V-30 Schottky Diodes

#### **FEATURES**

High current rectifier Schottky diode Low voltage, low inductance For power supply

MARKING: D





## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Single Diode @  $T_A = 25^{\circ}C$ 

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	30	V
DC reverse voltage	V <sub>R</sub>	20	V
Mean rectifying current	I <sub>O</sub>	0.5	А
Peak forward surge current	I <sub>FSM</sub>	2	A
Junction temperature	Tj	125	°C
Storage temperature	T <sub>stg</sub>	T <sub>stg</sub> -40~+125	

#### **ELECTRICAL RATINGS**

@ T<sub>A</sub> = 25<sup>o</sup>C

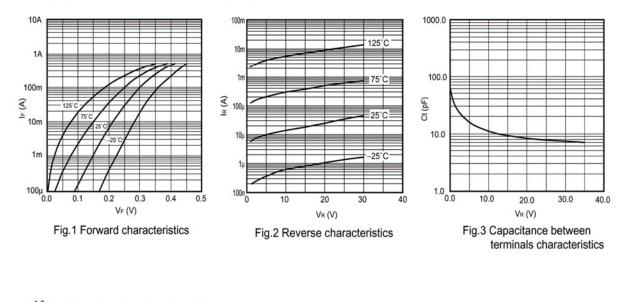
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>			0.36	V	I <sub>F</sub> =100mA
				0.47		I <sub>F</sub> =500mA
Reverse current	I <sub>R</sub>			100	μA	V <sub>R</sub> =20V



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## **TYPICAL CHARACTERISTICS**

Electrical Characteristic curves ( $T_a = 25^{\circ}C$ )



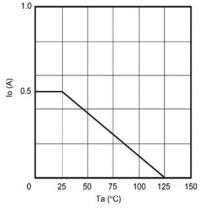


Fig.4 Derating curve

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